DGTD120T25S1PT

1200V FIELD STOP IGBT IN TO-247

Description

The DGTD120T25S1PT is produced using advanced Field Stop Trench IGBT Technology, which provides low $V_{CE(sat)}$, excellent quality and high-switching performance.

Features

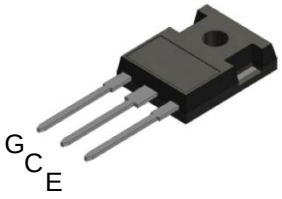
- High Speed Switching & Low $V_{CE(sat)}$ Loss
- $V_{CE(sat)}$ = 2.0V @ I_C = 25A
- High Input Impedance
- t_{rr} = 100ns (typ) @ di_F/dt = 500A/µs
- Ultra-Soft, Fast Recovery Anti-parallel Diode
- Ultra Narrowed VF Distribution Control
- Positive Temperature Coefficient For Easy Parallelling
- Maximum Junction Temperature 175°C
- **Lead-Free Finish & RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Applications

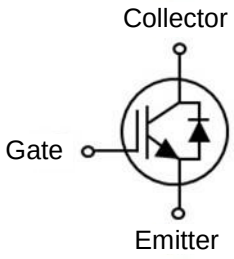
- Motor Drive
- UPS
- Welder
- Solar Inverter
- IH Cooker

Mechanical Data

- Case: TO-247 (Type MC)
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Terminals: Finish – Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 e3
- Weight: 5.6 grams (Approximate)



TO-247



Device Symbol

Ordering Information (Note 4)

Product	Marking	Quantity
DGTD120T25S1PT	DGTD120T25S1	450 per Box in Tubes (Note 5)

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
5. 30 Devices per Tube.

Marking Information

= Manufacturer's Marking
DGTD120T25S1 = Product Type Marking Code
YY = Year (ex: 18 = 2018)
LLLLL = Lot Code
WW = Week (01 to 53)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Collector-Emitter Voltage		V_{CE}	1,200	V
DC Collector Current, limited by T_{vjmax}	T_C = 25°C	I_C	50	A
	T_C = 100°C		25	A
Pulsed Collector Current, t_p limited by T_{vjmax}		I_{Cpuls}	100	A
Turn Off Safe Operating Area $V_{CE} \leq$ 1200V, T_{vj} = 175°C		-	100	A
Diode Forward Current limited by T_{vjmax}	T_C = 25°C	I_F	25	A
	T_C = 100°C		12.5	A
Diode Pulsed Current, t_p limited by T_{vjmax}		I_{Fpuls}	100	A
Gate-Emitter Voltage		V_{GE}	±20	V
Short Circuit Withstand Time $V_{CC} \leq$ 600V, V_{GE} = 15V, T_{vj} = 175°C Allowed Number of Short Circuits < 1000 Time Between Short Circuits ≥ 1.0s		tsc	10	µs

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 6)	T_C = 25°C	P_D	348	W
	T_C = 100°C		174	
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction to Case for IBGT (Note 6)		$R_{\theta JC}$	0.43	
Thermal Resistance, Junction to Case for Diode (Note 6)		$R_{\theta JC}$	1.55	
Operating Temperature		T_{vj}	-40 to +175	°C
Storage Temperature Range		T_{STG}	-55 to +150	

Note: 6. When mounted on a standard JEDEC 2-layer FR-4 board.

Electrical Characteristics (@T_{vj} = +25°C, unless otherwise specified.)

Parameter		Symbol	Min	Typ	Max	Unit	Condition
STATIC CHARACTERISTICS							
Collector-Emitter Breakdown Voltage		BV_{CES}	1200	–	–	V	I_C = 500μA, V_{GE} = 0V
Collector-Emitter Saturation Voltage	T_{vj} = 25°C	$V_{CE(sat)}$	–	2.00	2.40	V	I_C = 25A, V_{GE} = 15V
	T_{vj} = 150°C		–	2.40	–		
	T_{vj} = 175°C		–	2.50	–		
Diode Forward Voltage	T_{vj} = 25°C	V_F	–	2.10	2.60	V	V_{GE} = 0V, I_F = 12.5A
	T_{vj} = 175°C		–	1.90	–		
Diode Forward Voltage	T_{vj} = 25°C	V_F	–	2.50	3.00	V	V_{GE} = 0V, I_F = 25A
	T_{vj} = 150°C		–	2.55	–		
	T_{vj} = 175°C		–	2.45	–		
Gate-Emitter Threshold Voltage		$V_{GE(th)}$	5.0	6.0	7.0	V	V_{CE} = V_{GE}, I_C = 0.85mA
Zero Gate Voltage Collector Current	T_{vj} = 25°C	I_{CES}	–	–	250	μA	V_{CE} = 1200V, V_{GE} = 0V
	T_{vj} = 175°C		–	–	2500		
Gate-Emitter Leakage Current		I_{GES}	–	–	±250	nA	V_{GE} = 20V, V_{CE} = 0V
Transconductance		g_{fs}	–	16	–	S	V_{CE} = 20V, I_C = 25A
DYNAMIC CHARACTERISTICS							
Total Gate Charge		Q_g	–	204	–	nC	V_{CE} = 960V, I_C = 25A, V_{GE} = 15V
Gate-Emitter Charge		Q_{ge}	–	34	–		
Gate-Collector Charge		Q_{gc}	–	94	–		
Input Capacitance		C_{ies}	–	3942	–	pF	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz
Reverse Transfer Capacitance		C_{res}	–	72	–		
Output Capacitance		C_{oes}	–	142	–		
Internal Emitter Inductance Measured 5mm (0.197") From Case		L_E	–	13	–	nH	–
Short Circuit Collector Current Max. 1000 Short Circuits. Time Between Short Circuits ≥ 1.0s		$I_{C(SC)}$	–	121	–	A	V_{GE} = 15V, V_{CC} = 600V, t_{SC} ≤ 10μs, T_{vj} = 175°C
SWITCHING CHARACTERISTICS							
Turn-on Delay Time		$t_{d(on)}$	–	73	–	ns	V_{GE} = 15V, V_{CC} = 600V, I_C = 25A, R_G = 23Ω, Inductive Load, T_{vj} = 25°C
Rise time		t_r	–	41	–		
Turn-off Delay Time		$t_{d(off)}$	–	269	–		
Fall Time		t_f	–	39	–		
Turn-on Switching Energy		E_{on}	–	1.44	–	mJ	
Turn-off Switching Energy		E_{off}	–	0.55	–		
Total Switching Energy		E_{ts}	–	1.99	–		
Reverse Recovery Time		t_{rr}	–	100	–	ns	I_F = 25A, di_F/dt = 500A/μs, V_R = 600V, T_{vj} = 25°C
Reverse Recovery Current		I_{rr}	–	17	–	A	
Reverse Recovery Charge		Q_{rr}	–	0.85	–	μC	
Rate Of Fall Of Reverse Current During t_b		di_{rr}/dt	–	-376	–	A/μs	
Turn-on Delay Time		$t_{d(on)}$	–	65	–	ns	V_{GE} = 15V, V_{CC} = 600V, I_C = 25A, R_G = 23Ω, Inductive Load, T_{vj} = 175°C
Rise time		t_r	–	45	–		
Turn-off Delay Time		$t_{d(off)}$	–	292	–		
Fall Time		t_f	–	75	–		
Turn-on Switching Energy		E_{on}	–	2.43	–	mJ	
Turn-off Switching Energy		E_{off}	–	1.09	–		
Total Switching Energy		E_{ts}	–	3.52	–		
Reverse Recovery Time		t_{rr}	–	150	–	ns	I_F = 25A, di_F/dt = 500A/μs, V_R = 600V, T_{vj} = 175°C
Reverse Recovery Current		I_{rr}	–	25	–	A	
Reverse Recovery Charge		Q_{rr}	–	1.85	–	μC	
Rate Of Fall Of Reverse Current During t_b		di_{rr}/dt	–	-374	–	A/μs	

Typical Performance Characteristics (@T_A = +25°C, unless otherwise specified.)

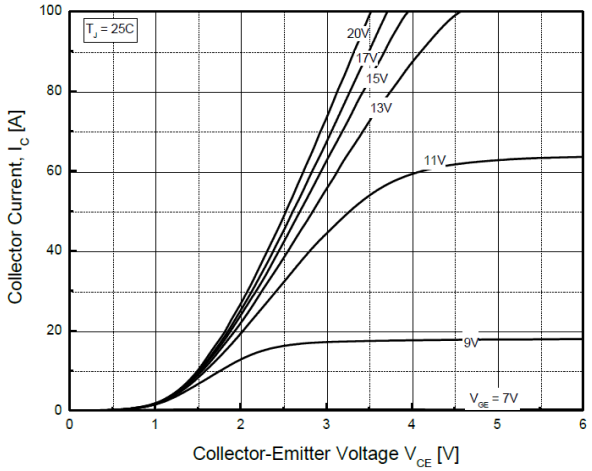


Fig.1 Typical Output Characteristic(T_J=25°C)

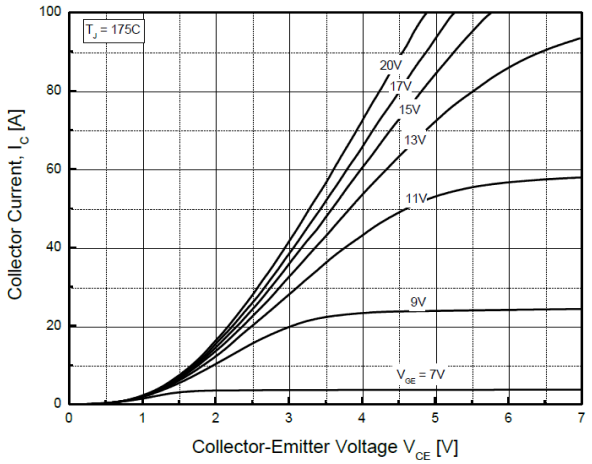


Fig.2 Typical Output Characteristic(T_J=175°C)

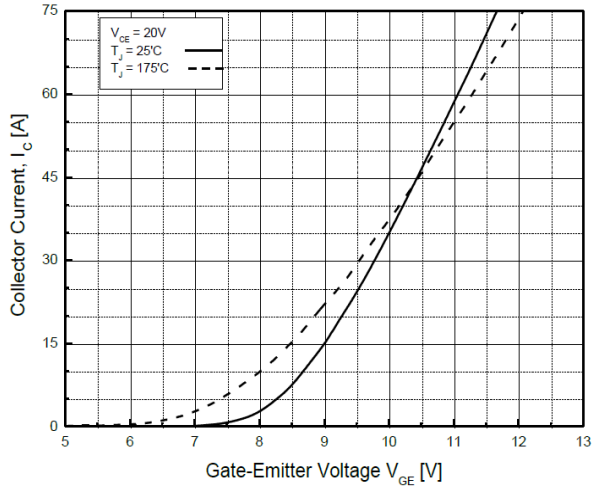


Fig.3 Typical Transfer Characteristic

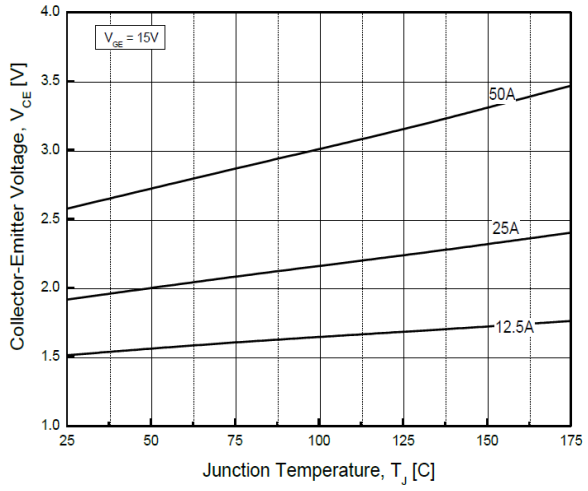


Fig.4 Typical Collector-Emitter Saturation Voltage -Junction Temperature

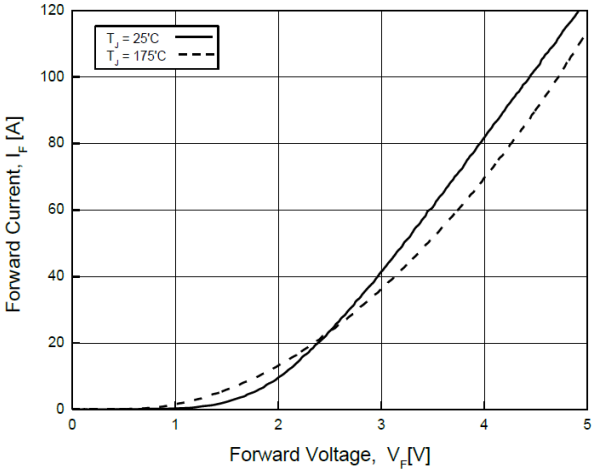


Fig.5 Diode Forward Characteristic

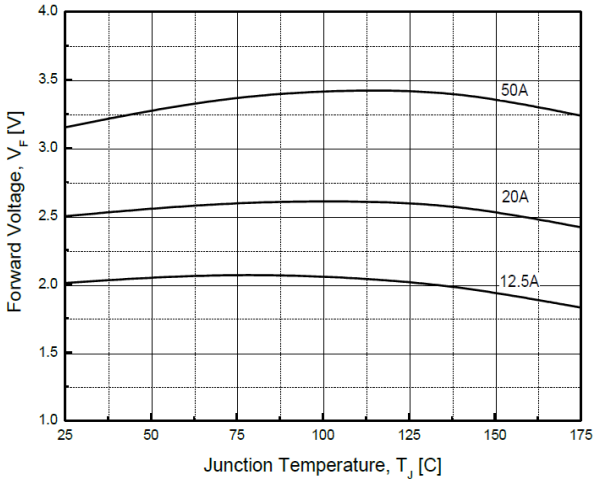


Fig.6 Diode Forward-Junction Temperature

Typical Performance Characteristics (continued)

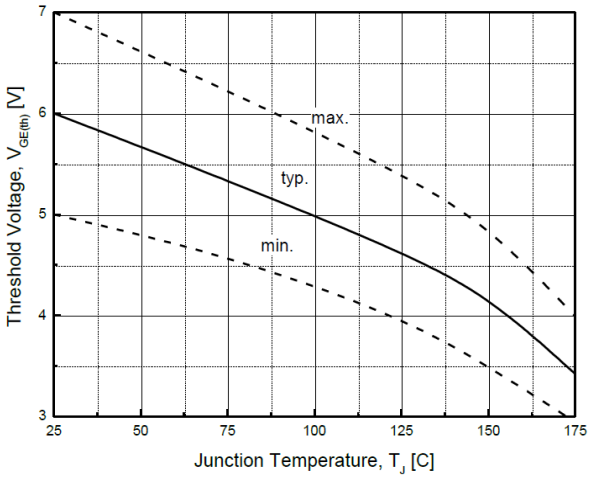


Fig.7 Threshold Voltage-Junction Temperature

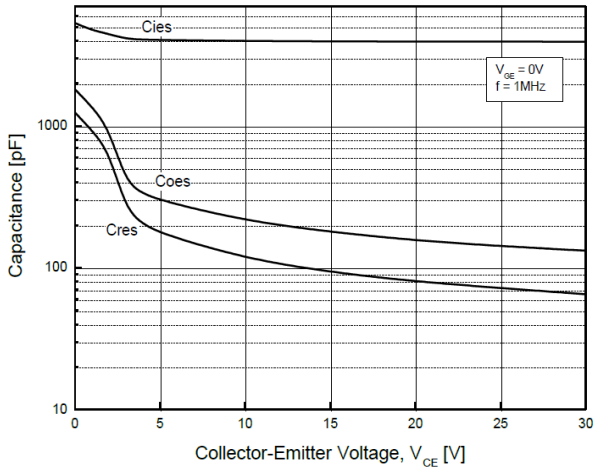


Fig.8 Typical Capacitance

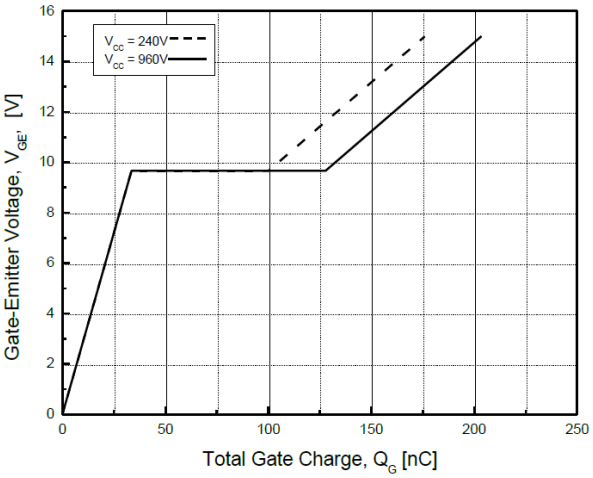


Fig.9 Typical Gate Charge

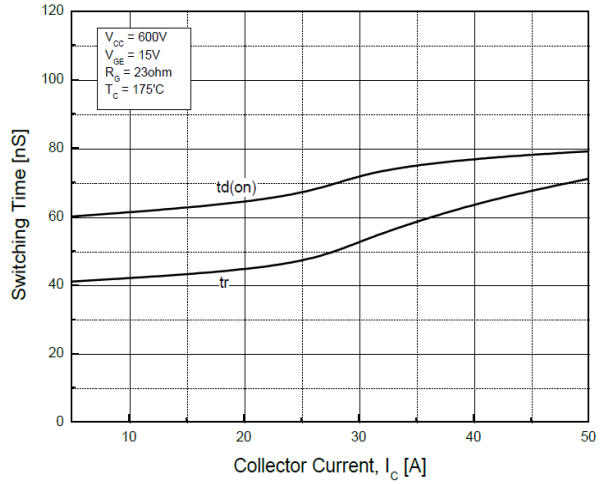


Fig.10 Typical Turn on-Collector Current

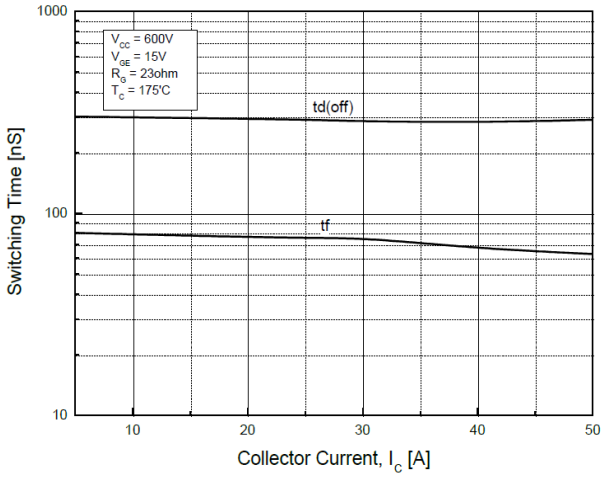


Fig.11 Typical Turn off-Collector Current

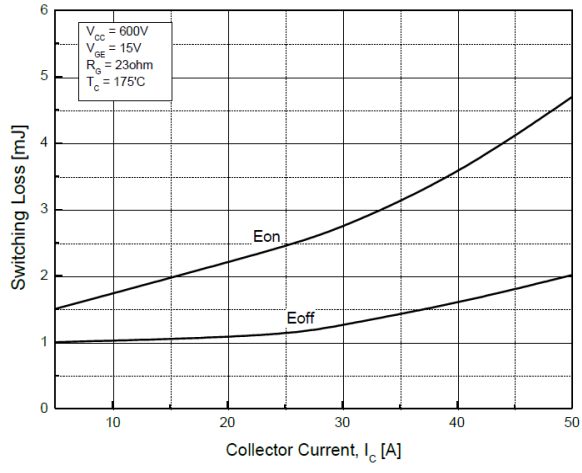


Fig.12 Switching Loss-Collector Current

Typical Performance Characteristics (cont.)

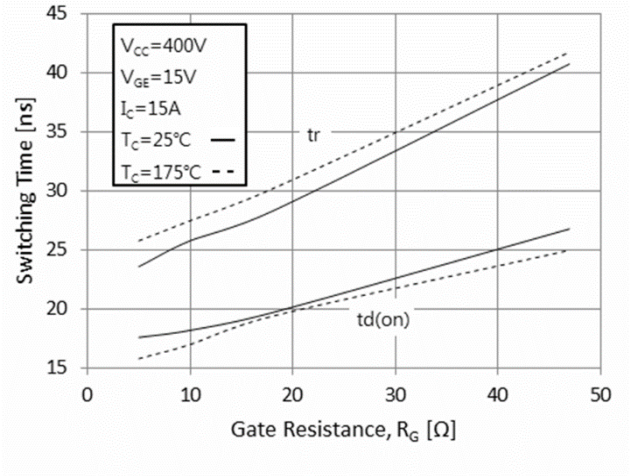


Fig.13 Turn on Characteristics-Gate Resistance

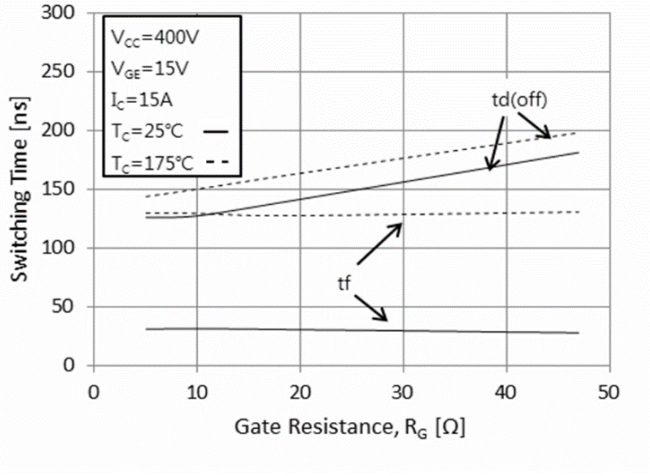


Fig.14 Turn off Characteristics-Gate Resistance

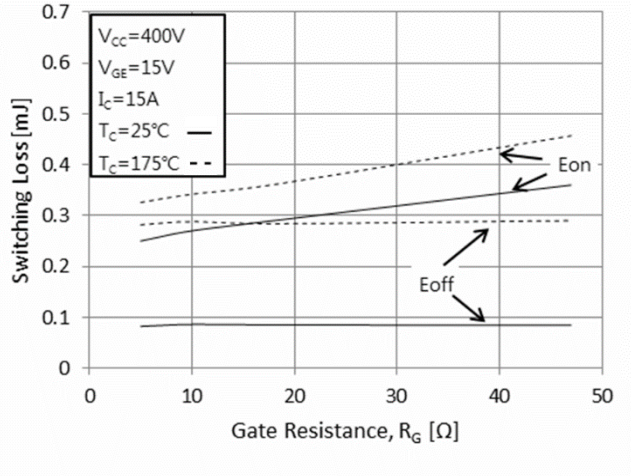


Fig.15 Switching Loss-Gate Resistance

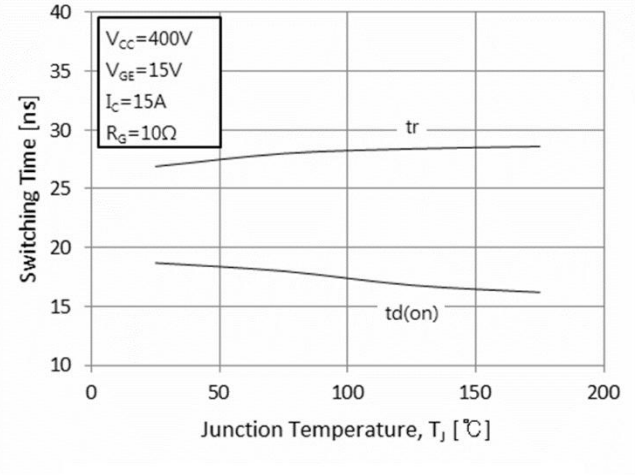


Fig.16 Turn on Characteristics-Junction Temperature

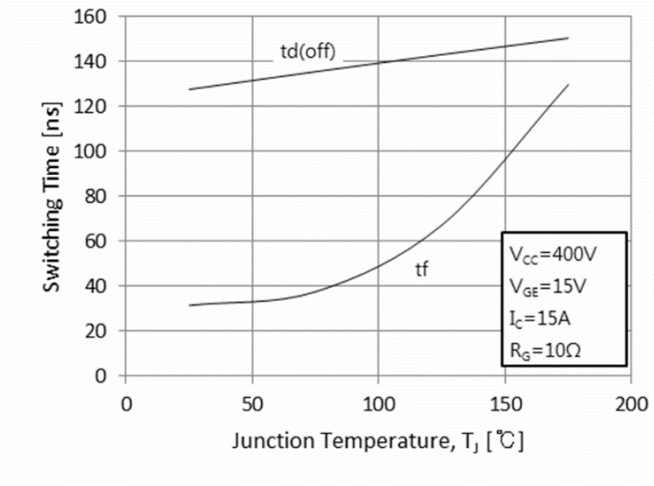


Fig.17 Turn off Characteristics-Junction Temperature

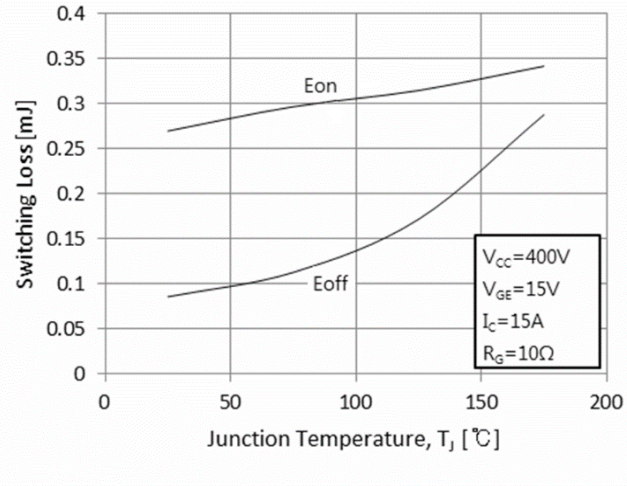


Fig.18 Switching Loss-Junction Temperature

Typical Performance Characteristics (cont.)

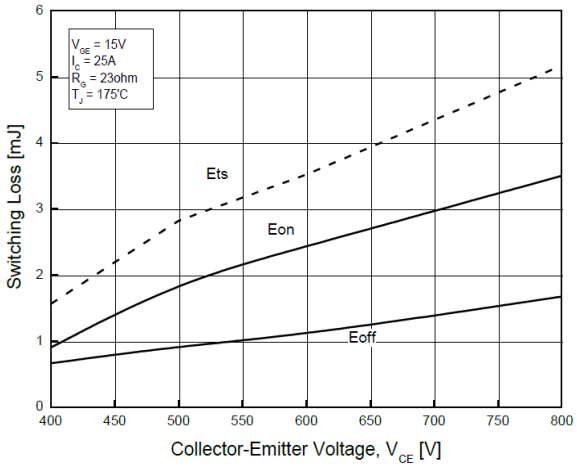


Fig.19 Switching Loss-Collector Emitter Voltage

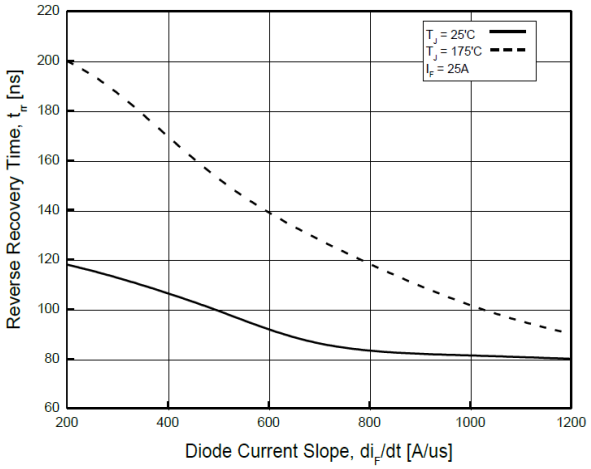


Fig.20 Reverse Recovery Time -Diode current slope

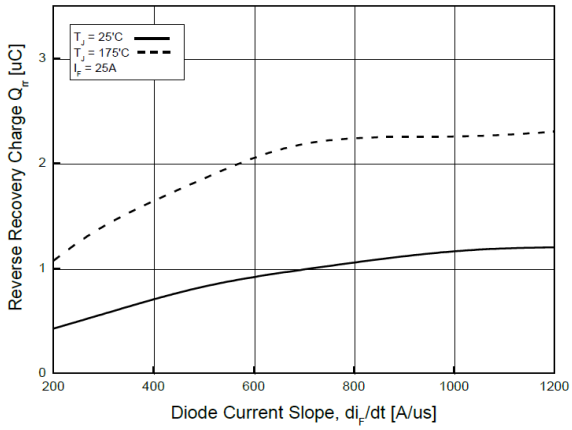


Fig.21 Reverse Recovery Charge -Diode Current Slope

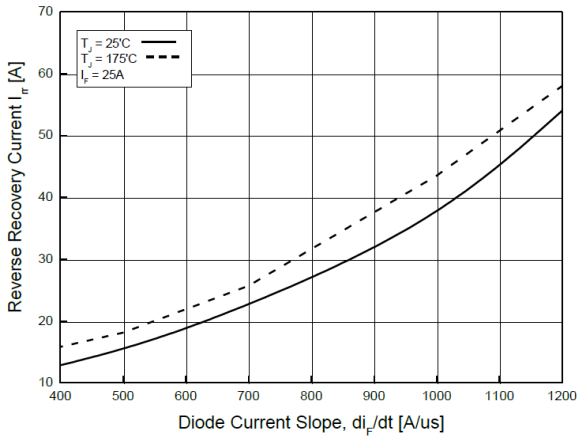


Fig.22 Reverse Recovery Current -Diode current slope

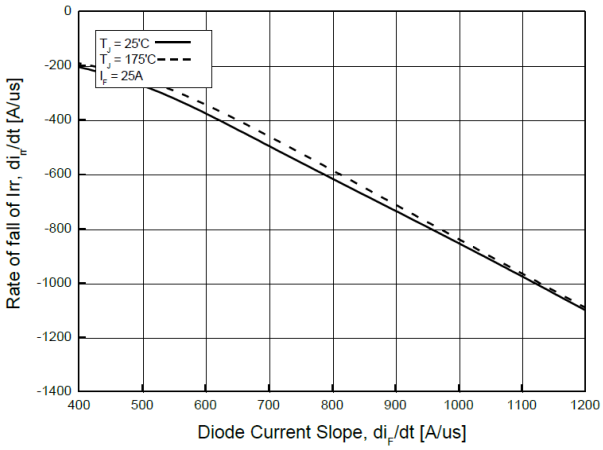


Fig.23 Rate of fall of reverse recovery current -Diode Current Slope

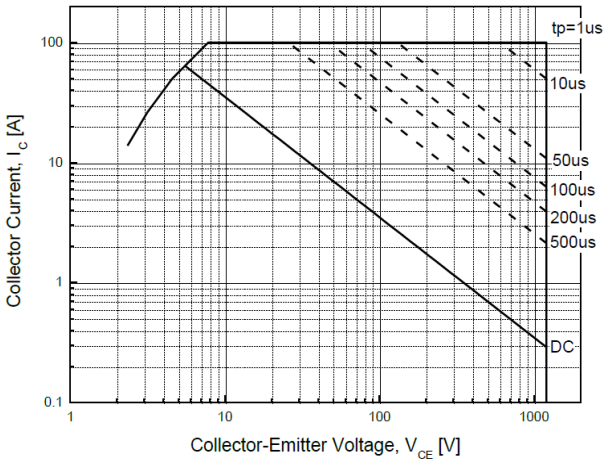


Fig.24 Forward Bias Safe Operating Area

Typical Performance Characteristics (cont.)

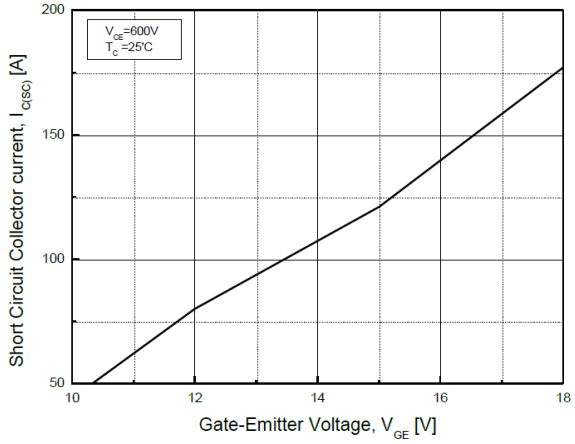


Fig.25 Typical Short Circuit Collector Current

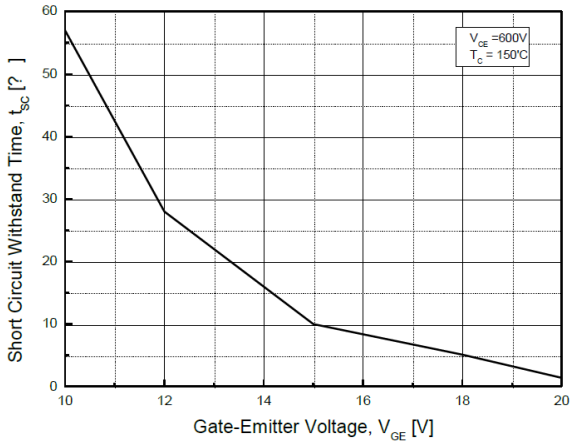


Fig.26 Typical Short Circuit Withstand Time

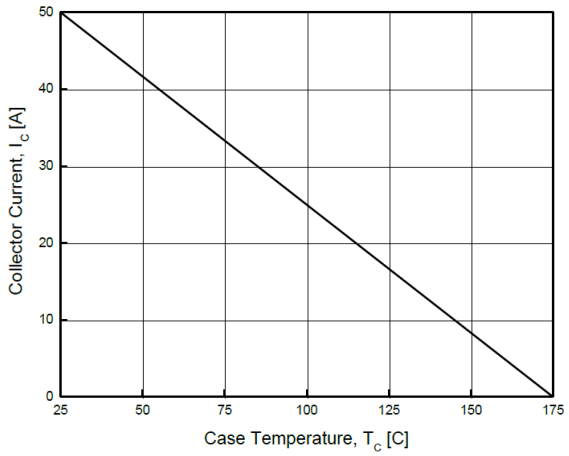


Fig.27 Case Temperature-Collector Current

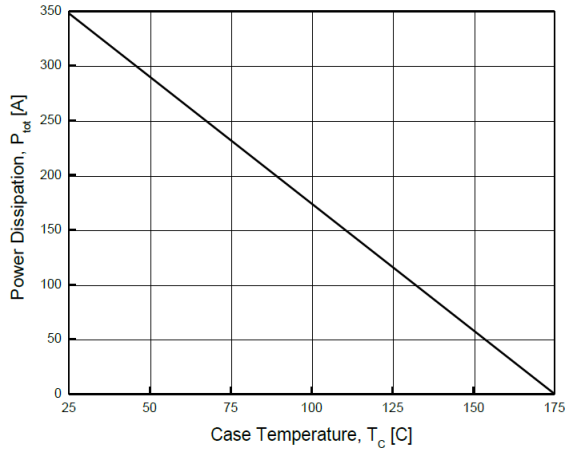


Fig.28 Power Dissipation-Case Temperature

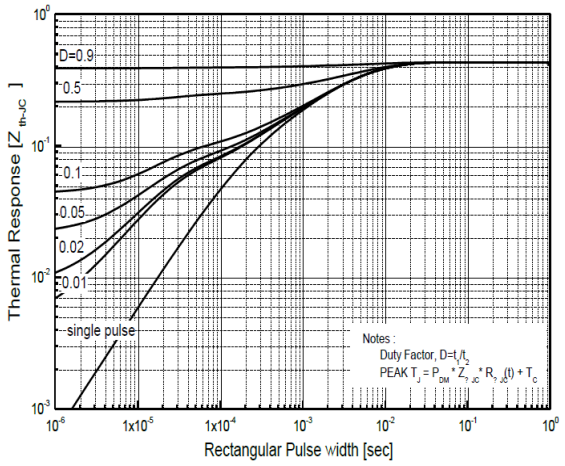


Fig.29 IGBT Transient Thermal Impedance

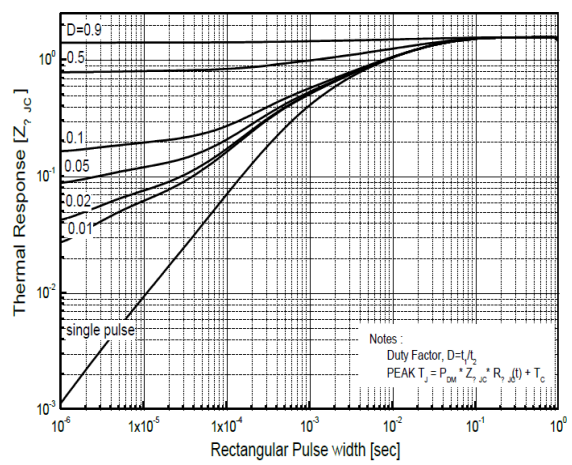
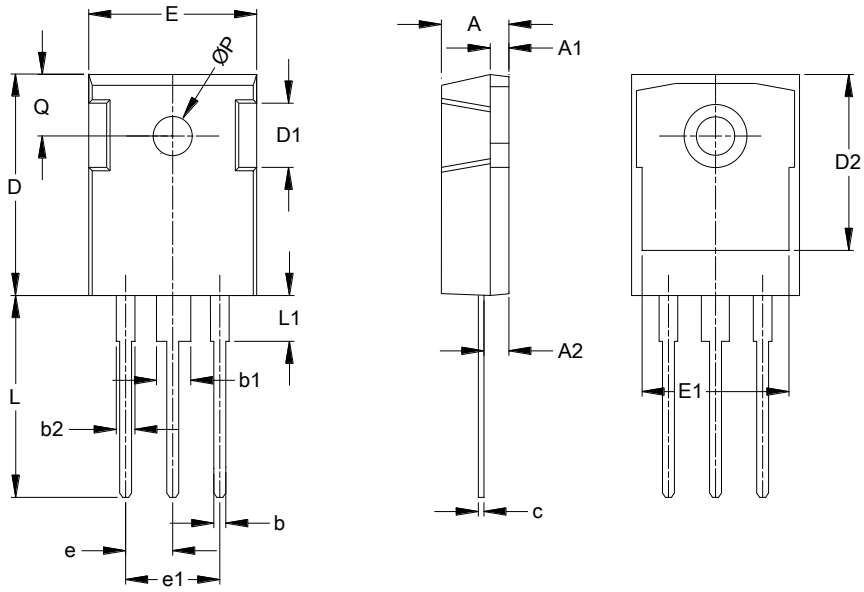


Fig.30 FRD Transient Thermal Impedance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO-247 (Type MC)



TO-247 (Type MC)			
Dim	**Min**	**Max**	**Typ**
A	4.700	5.310	-
A1	1.500	2.490	-
A2	2.200	2.600	-
b	0.990	1.400	-
b1	2.590	3.430	-
b2	1.650	2.390	-
c	0.380	0.890	-
D	20.30	21.46	-
D1	4.320	5.490	-
D2	13.08	-	-
E	15.45	16.26	-
E1	13.06	14.02	-
e	5.450		
e1	10.90		
L	19.81	20.57	-
L1	-	4.500	-
Q	5.380	6.200	-
øP	3.500	3.700	-
All Dimensions in mm			

Note : For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or

2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for IGBT Transistors ***category:***

Click to view products by Diodes Incorporated ***manufacturer:***

Other Similar products are found below :

748152A FGH60T65SHD_F155 APT100GT60B2RG APT13GP120BG APT15GN120BDQ1G APT15GP90BDQ1G APT20GN60BG APT20GT60BRDQ1G APT25GN120B2DQ2G APT35GA90BD15 APT36GA60BD15 APT40GP60B2DQ2G APT40GP90B2DQ2G APT50GN120B2G APT50GT60BRG APT64GA90B2D30 APT70GR120J NGTB10N60FG NGTB30N60L2WG IGP30N60H3XKSA1 IGW40N60H3FKSA1 IXGK50N60B NRND STGB15H60DF STGFW20V60DF STGFW30V60DF STGFW40V60F STGWA25H120DF2 FGB3236_F085 APT13GP120BDQ1G APT25GN120BG APT25GR120S APT30GN60BDQ2G APT30GN60BG APT30GP60BG APT30GS60BRDQ2G APT30N60BC6 APT35GP120JDQ2 APT36GA60B APT45GR65B2DU30 APT50GP60B2DQ2G APT68GA60B APT70GR65B APT70GR65B2SCD30 GT50JR22(STA1ES) IDW40E65D2 SGB15N120ATMA1 NGTB50N60L2WG STGB10H60DF STGB20V60F STGB40V60F